

# P2N2222A

## Amplifier Transistors

### NPN Silicon

#### Features

- These are Pb-Free Devices\*

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector – Base Voltage	$V_{CBO}$	75	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	600	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

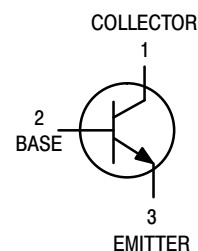
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

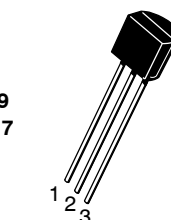


ON Semiconductor®

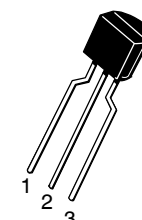
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TO-92  
CASE 29  
STYLE 17

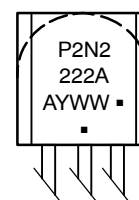


STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

#### MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# P2N2222A

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	V <sub>dc</sub>
Collector – Base Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	75	–	V <sub>dc</sub>
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 60 V <sub>dc</sub> , V <sub>EB(off)</sub> = 3.0 V <sub>dc</sub> )	I <sub>CEX</sub>	–	10	nA <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 60 V <sub>dc</sub> , I <sub>E</sub> = 0) (V <sub>CB</sub> = 60 V <sub>dc</sub> , I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	– –	0.01 10	μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	10	nA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 10 V)	I <sub>CEO</sub>	–	10	nA <sub>dc</sub>
Base Cutoff Current (V <sub>CE</sub> = 60 V <sub>dc</sub> , V <sub>EB(off)</sub> = 3.0 V <sub>dc</sub> )	I <sub>BEX</sub>	–	20	nA <sub>dc</sub>

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , T <sub>A</sub> = –55°C) (I <sub>C</sub> = 150 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (Note 1) (I <sub>C</sub> = 150 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (Note 1) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (Note 1)	h <sub>FE</sub>	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.3 1.0	V <sub>dc</sub>
Base – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	0.6 –	1.2 2.0	V <sub>dc</sub>

## SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 20 mA <sub>dc</sub> , V <sub>CE</sub> = 20 V <sub>dc</sub> , f = 100 MHz) <sub>C</sub>	f <sub>T</sub>	300	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	25	pF
Input Impedance (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>re</sub>	– –	8.0 4.0	X 10 <sup>–4</sup>
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	50 75	300 375	–
Output Admittance (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	5.0 25	35 200	μMhos
Collector Base Time Constant (I <sub>E</sub> = 20 mA <sub>dc</sub> , V <sub>CB</sub> = 20 V <sub>dc</sub> , f = 31.8 MHz)	rb'C <sub>c</sub>	–	150	ps
Noise Figure (I <sub>C</sub> = 100 μA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	N <sub>F</sub>	–	4.0	dB

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

# P2N2222A

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>SWITCHING CHARACTERISTICS</b>				
Delay Time	$t_d$	—	10	ns
Rise Time	$t_r$	—	25	ns
Storage Time	$t_s$	—	225	ns
Fall Time	$t_f$	—	60	ns

## SWITCHING TIME EQUIVALENT TEST CIRCUITS

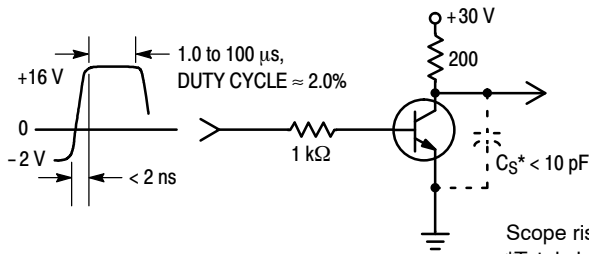


Figure 1. Turn-On Time

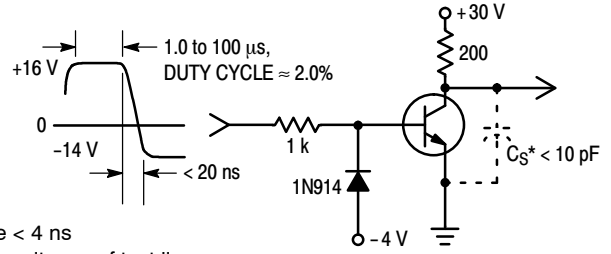


Figure 2. Turn-Off Time

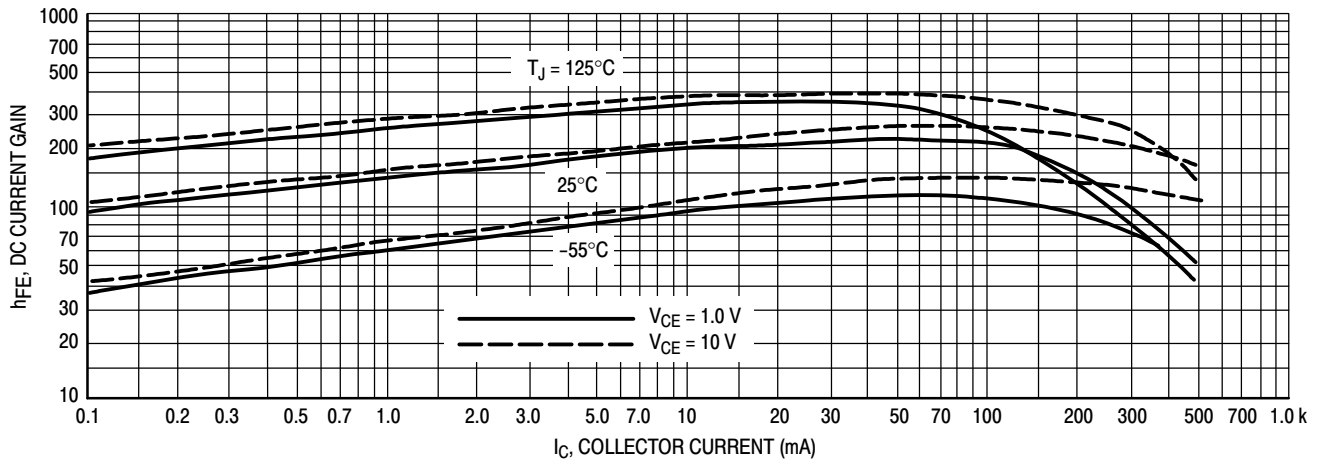
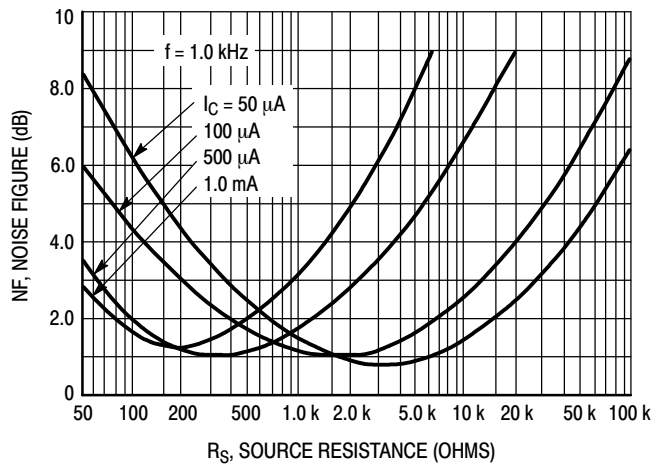
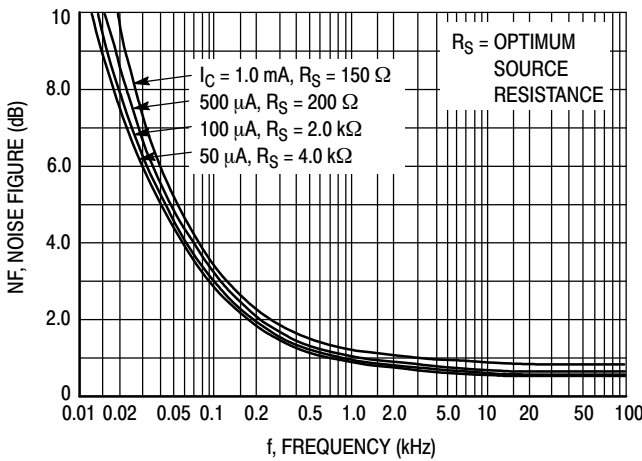
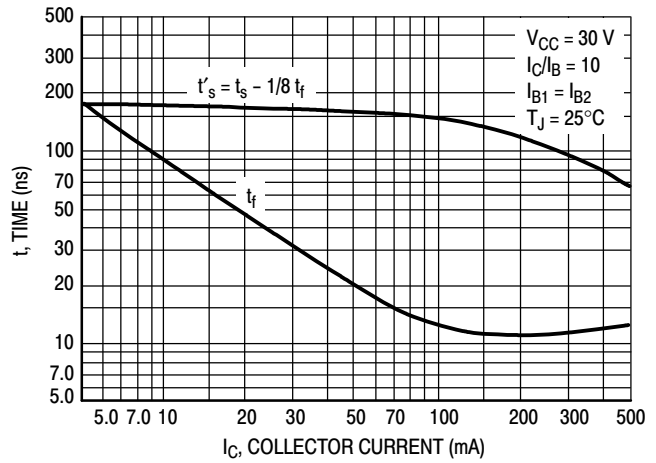
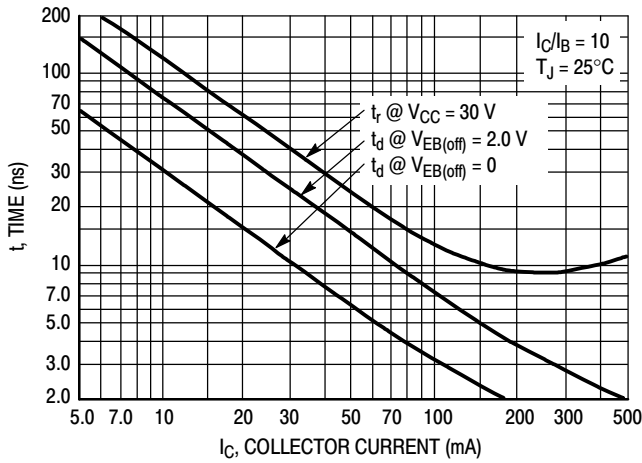
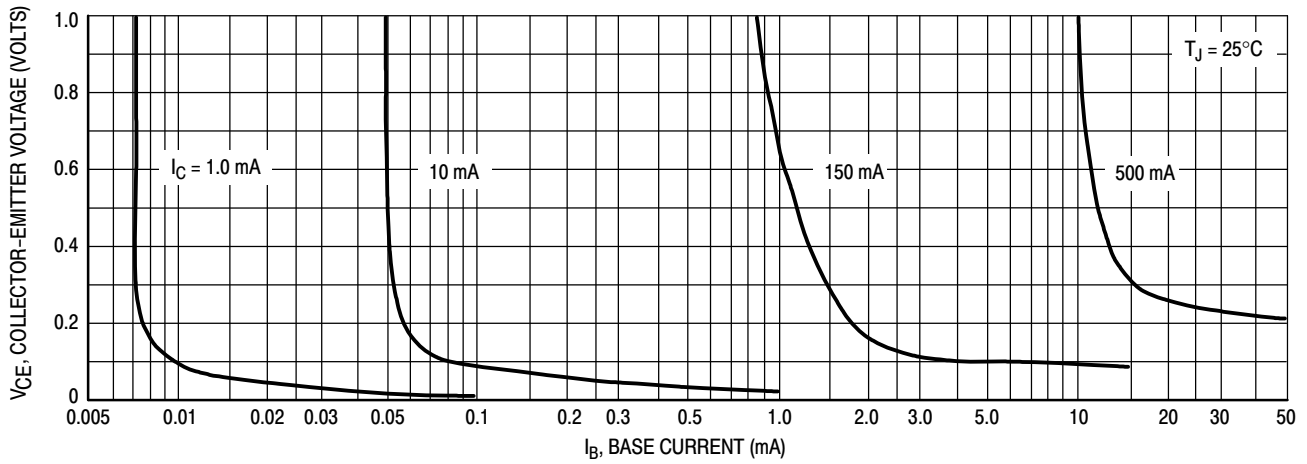


Figure 3. DC Current Gain

# P2N2222A



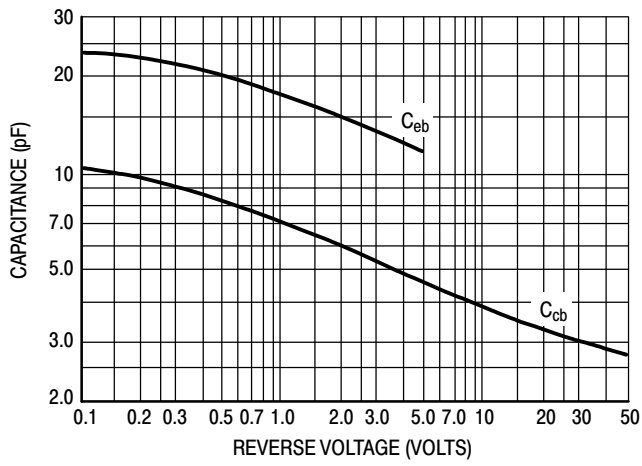


Figure 9. Capacitances

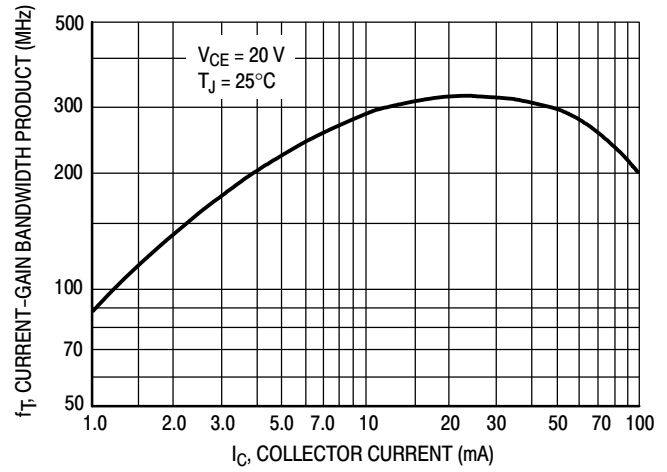


Figure 10. Current-Gain Bandwidth Product

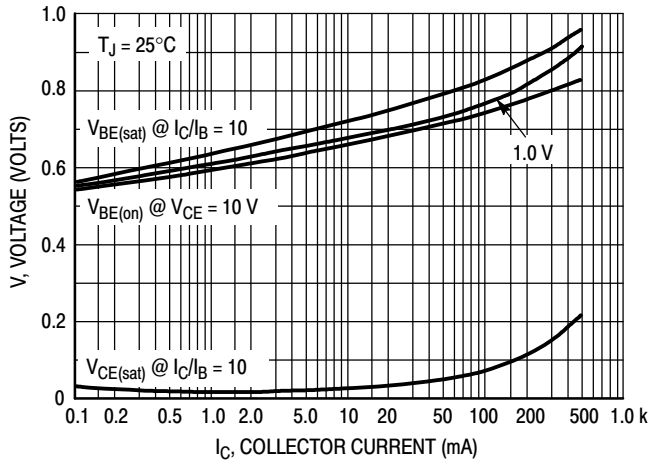


Figure 11. "On" Voltages

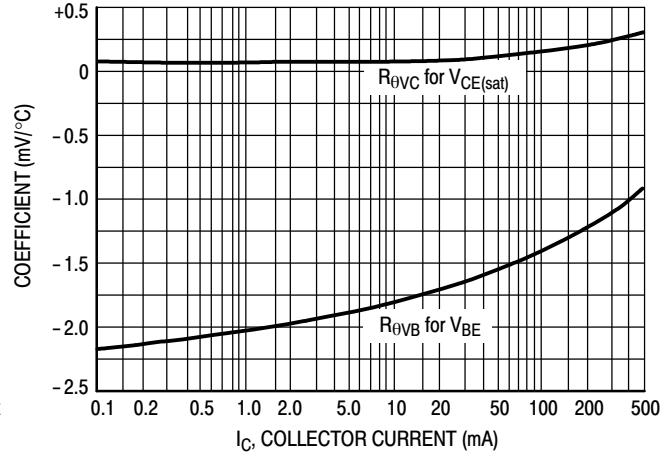
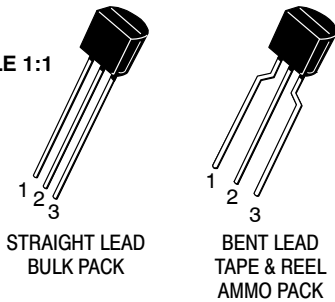


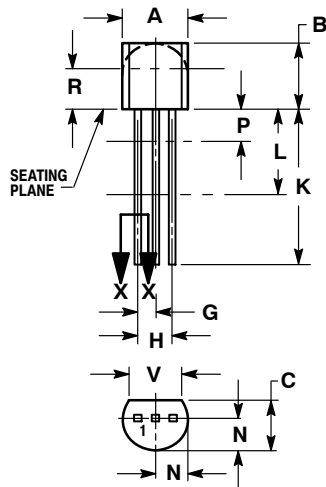
Figure 12. Temperature Coefficients

SCALE 1:1

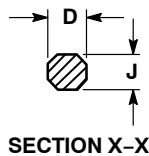


TO-92 (TO-226)  
CASE 29-11  
ISSUE AM

DATE 09 MAR 2007



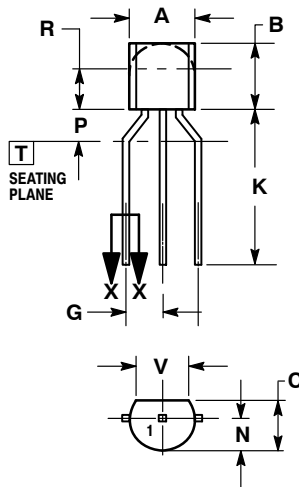
STRAIGHT LEAD  
BULK PACK



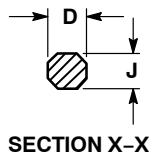
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

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**TO-92 (TO-226)**  
**CASE 29-11**  
**ISSUE AM**

DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. $V_{CC}$ 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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